2SD2453

Silicon NPN triple diffusion planar type

For high current transfer ratio and power amplification

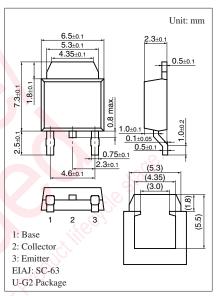
■ Features

- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage V_{CE(sat)}

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	80	V	
Collector-emitter voltage (Base open)	V_{CEO}	60	V	
Emitter-base voltage (Collector open)	V_{EBO}	6	V	
Collector current	I_{C}	2	A	
Peak collector current *	I_{CP}	4	A	
Base current	I_{B}	1	A	
Collector power $T_C = 25^{\circ}C$	P_{C}	10	W	
dissipation		1		
Junction temperature	Tj	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	

Note) Non-repetitive peak collector current



Note) Self-supported type package is also prepared.

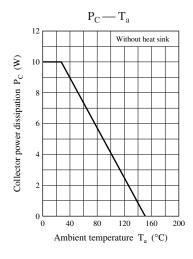
■ Electrical Characteristics T_a = 25°C

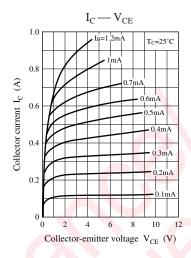
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 25 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 80 \text{ V}, I_{E} = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 40 \text{ V}, I_{B} = 0$			100	μΑ
Emiter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 6 \text{ V}, I_C = 0$			100	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = 4 \text{ V}, I_{C} = 0.5 \text{ A}$	500		2500	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 2 A, I_B = 0.05 A$			1	V
Transition frequency	f_T	$V_{CE} = 12 \text{ V}, I_C = 0.2 \text{ A}, f = 10 \text{ MHz}$		50		MHz

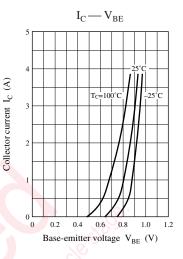
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

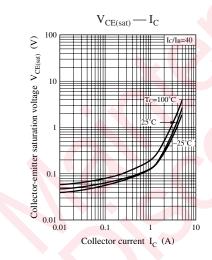
2. *: Rank classification

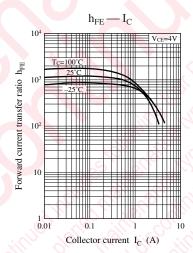
Rank	Q	R	S
h_{FE}	500 to 1 000	800 to 1500	1 200 to 2 500

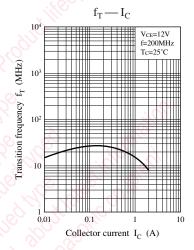


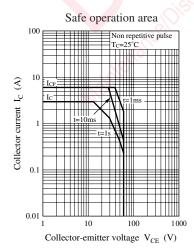












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